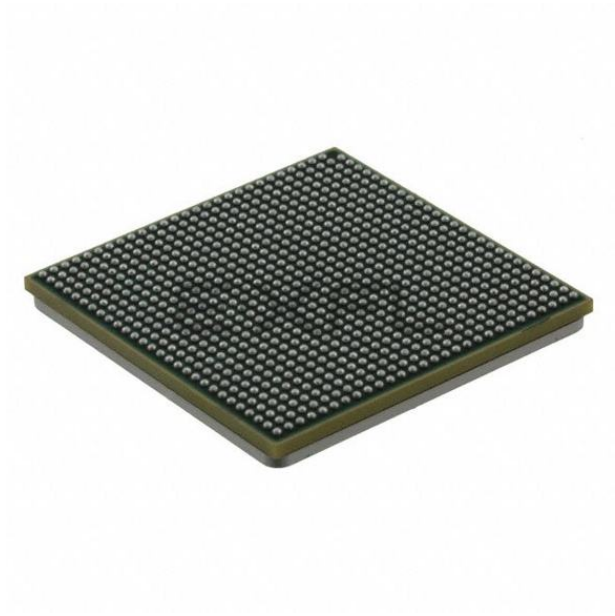

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Understanding Embedded - Microprocessors

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Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500v2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.067GHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2, DDR3, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (8), 1Gbps (4)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.0V, 1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8569vjaqljb

Table 1. MPC8569E Pinout Listing (continued)

Signal[1]	Package Pin Number	Pin Type	Power Supply	Note
D1_MDQ22	J26	I/O	GV_{DD}	—
D1_MDQ23	J25	I/O	GV_{DD}	—
D1_MDQ24	C24	I/O	GV_{DD}	—
D1_MDQ25	C22	I/O	GV_{DD}	—
D1_MDQ26	C21	I/O	GV_{DD}	—
D1_MDQ27	B21	I/O	GV_{DD}	—
D1_MDQ28	B24	I/O	GV_{DD}	—
D1_MDQ29	A24	I/O	GV_{DD}	—
D1_MDQ30	A22	I/O	GV_{DD}	—
D1_MDQ31	A21	I/O	GV_{DD}	—
D1_MDQS0	D26	I/O	GV_{DD}	—
$\overline{\text{D1\_MDQS0}}$	C26	I/O	GV_{DD}	—
D1_MDQS1	H26	I/O	GV_{DD}	—
$\overline{\text{D1\_MDQS1}}$	G26	I/O	GV_{DD}	—
D1_MDQS2	K24	I/O	GV_{DD}	—
$\overline{\text{D1\_MDQS2}}$	L25	I/O	GV_{DD}	—
D1_MDQS3	D23	I/O	GV_{DD}	—
$\overline{\text{D1\_MDQS3}}$	C23	I/O	GV_{DD}	—
D1_MDQS8	H23	I/O	GV_{DD}	—
$\overline{\text{D1\_MDQS8}}$	G23	I/O	GV_{DD}	—
D1_MECC0	G24	I/O	GV_{DD}	—
D1_MECC1	H22	I/O	GV_{DD}	—
D1_MECC2	G22	I/O	GV_{DD}	—
D1_MECC3	F21	I/O	GV_{DD}	—
D1_MECC4	F24	I/O	GV_{DD}	—
D1_MECC5	D22	I/O	GV_{DD}	—
D1_MECC6	E21	I/O	GV_{DD}	—
D1_MECC7	D21	I/O	GV_{DD}	—
D1_MODT0	C16	O	GV_{DD}	—
D1_MODT1	J16	O	GV_{DD}	—
D1_MODT2	G17	O	GV_{DD}	—
D1_MODT3	E16	O	GV_{DD}	—
D1_MAPAR_OUT	E15	O	GV_{DD}	—
$\overline{\text{D1\_MAPAR\_ERR}}$	F15	I	GV_{DD}	—
$\overline{\text{D1\_MRAS}}$	G18	O	GV_{DD}	—

Table 1. MPC8569E Pinout Listing (continued)

Signal[1]	Package Pin Number	Pin Type	Power Supply	Note
D2_MDQ28/D1_MDQ60	B10	I/O	GV_{DD}	—
D2_MDQ29/D1_MDQ61	A10	I/O	GV_{DD}	—
D2_MDQ30/D1_MDQ62	A8	I/O	GV_{DD}	—
D2_MDQ31/D1_MDQ63	A7	I/O	GV_{DD}	—
D2_MDQS0/D1_MDQS4	C12	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS0}}$/$\overline{\text{D1\_MDQS4}}$	C13	I/O	GV_{DD}	—
D2_MDQS1/D1_MDQS5	G12	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS1}}$/$\overline{\text{D1\_MDQS5}}$	F12	I/O	GV_{DD}	—
D2_MDQS2/D1_MDQS6	J13	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS2}}$/$\overline{\text{D1\_MDQS6}}$	K14	I/O	GV_{DD}	—
D2_MDQS3/D1_MDQS7	D9	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS3}}$/$\overline{\text{D1\_MDQS7}}$	C9	I/O	GV_{DD}	—
D2_MDQS8	H9	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS8}}$	G9	I/O	GV_{DD}	—
D2_MECC0	G10	I/O	GV_{DD}	—
D2_MECC1	H8	I/O	GV_{DD}	—
D2_MECC2	G8	I/O	GV_{DD}	—
D2_MECC3	F7	I/O	GV_{DD}	—
D2_MECC4	F10	I/O	GV_{DD}	—
D2_MECC5	D8	I/O	GV_{DD}	—
D2_MECC6	E7	I/O	GV_{DD}	—
D2_MECC7	D7	I/O	GV_{DD}	—
D2_MODT0	C1	O	GV_{DD}	—
D2_MODT1	A3	O	GV_{DD}	—
D2_MODT2	H3	O	GV_{DD}	—
D2_MODT3	E1	O	GV_{DD}	—
D2_MAPAR_OUT	F1	O	GV_{DD}	—
$\overline{\text{D2\_MAPAR\_ERR}}$	G1	I	GV_{DD}	—
$\overline{\text{D2\_MRAS}}$	G4	O	GV_{DD}	—
$\overline{\text{D2\_MWE}}$	E2	O	GV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK0}}$	AF23	O	OV_{DD}	2
$\overline{\text{DMA\_DACK1}}$/MSRCID1	AD27	O	OV_{DD}	11
$\overline{\text{DMA\_DACK2}}$/SD_CMD	AD24	O	OV_{DD}	—
$\overline{\text{DMA\_DDONE0}}$	AD25	O	OV_{DD}	2

Table 1. MPC8569E Pinout Listing (continued)

Signal[1]	Package Pin Number	Pin Type	Power Supply	Note
Power Management				
ASLEEP	M23	O	OV_{DD}	11
Thermal Management				
THERM0	U21	—	Internal temperature diode cathode	32
THERM1	U20	—	Internal temperature diode anode	32
Reserved	T22	—	—	9
Analog				
D1_MVREF	N27	Reference voltage for DDR	MV_{REF}	—
D2_MVREF	J1			—
Power and Ground				
V_{DD}	L13	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	L17	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	L19	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	M12	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	M14	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	M16	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	M18	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	N13	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	N15	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	N17	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	N19	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	P12	1.0-V/1.1-V core power supply	V_{DD}	—
V_{DD}	P16	1.0-V/1.1-V core power supply	V_{DD}	—

Table 1. MPC8569E Pinout Listing (continued)

Signal[1]	Package Pin Number	Pin Type	Power Supply	Note
$LV_{DD}1$	R4	3.3-/2.5-V Ethernet power supply	$LV_{DD}1$	—
$LV_{DD}1$	R6	3.3-/2.5-V Ethernet power supply	$LV_{DD}1$	—
$LV_{DD}1$	T10	3.3-/2.5-V Ethernet power supply	$LV_{DD}1$	—
$LV_{DD}2$	M10	3.3-/2.5-V Ethernet power supply	$LV_{DD}2$	—
$LV_{DD}2$	M3	3.3-/2.5-V Ethernet power supply	$LV_{DD}2$	—
$LV_{DD}2$	M7	3.3-/2.5-V Ethernet power supply	$LV_{DD}2$	—
OV_{DD}	AB9	3.3-V power supply	OV_{DD}	—
OV_{DD}	AC5	3.3-V power supply	OV_{DD}	—
OV_{DD}	AE11	3.3-V power supply	OV_{DD}	—
OV_{DD}	AE2	3.3-V power supply	OV_{DD}	—
OV_{DD}	AE27	3.3-V power supply	OV_{DD}	—
OV_{DD}	AF24	3.3-V power supply	OV_{DD}	—
OV_{DD}	AF7	3.3-V power supply	OV_{DD}	—
OV_{DD}	M26	3.3-V power supply	OV_{DD}	—
OV_{DD}	N23	3.3-V power supply	OV_{DD}	—
OV_{DD}	W10	3.3-V power supply	OV_{DD}	—
OV_{DD}	W6	3.3-V power supply	OV_{DD}	—
OV_{DD}	Y2	3.3-V power supply	OV_{DD}	—
ScoreVDD	AA28	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	AC27	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	R27	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	T25	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	U28	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	V26	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	W27	1.0-V/1.1-V SerDes power supply	ScoreVDD	—
ScoreVDD	Y25	1.0-V/1.1-V SerDes power supply	ScoreVDD	—

Table 1. MPC8569E Pinout Listing (continued)

Signal[1]	Package Pin Number	Pin Type	Power Supply	Note
GND	AF11	—	—	—
GND	AF2	—	—	—
GND	AG15	—	—	—
GND	AG17	—	—	—
GND	AG19	—	—	—
GND	AG21	—	—	—
GND	AG24	—	—	—
GND	AG7	—	—	—
GND	AH23	—	—	—
GND	AH25	—	—	—
GND	B13	—	—	—
GND	B17	—	—	—
GND	B20	—	—	—
GND	B23	—	—	—
GND	B27	—	—	—
GND	B3	—	—	—
GND	B6	—	—	—
GND	B9	—	—	—
GND	C4	—	—	—
GND	D11	—	—	—
GND	D16	—	—	—
GND	D19	—	—	—
GND	D2	—	—	—
GND	D25	—	—	—
GND	D28	—	—	—
GND	D5	—	—	—
GND	E13	—	—	—
GND	F17	—	—	—
GND	F20	—	—	—
GND	F23	—	—	—
GND	F27	—	—	—
GND	F3	—	—	—
GND	F6	—	—	—
GND	F9	—	—	—
GND	H1	—	—	—

Table 2. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Range	Unit	Notes
QUICC Engine block Ethernet interface I/O voltage		$LV_{DD}2$	–0.3 to 3.63 –0.3 to 2.75	V	—
Debug, DMA, DUART, PIC, I^2C, JTAG, power management, QUICC Engine block, eSDHC, GPIO, clocking, SPI, I/O voltage select and system control I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Enhanced local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 1.98	V	—
Input voltage	DDR2/DDR3 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 3
	DDR2/DDR3 DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	—
	Ethernet signals	LV_{IN}	–0.3 to ($LV_{DD}n$ + 0.3)	V	3
	Enhanced local bus signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	—	3
	Debug, DMA, DUART, PIC, I^2C, JTAG, power management, QUICC Engine block, eSDHC, GPIO, clocking, SPI, I/O voltage select and system control I/O voltage	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3
	SerDes signals	XV_{IN}	–0.3 to (XV_{DD} + 0.3)	V	—
Storage junction temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 3. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The –0.3 to 1.98 V range is for DDR2, and the –0.3 to 1.65 V range is for DDR3.
3. **Caution:** (B,M,L,O,X)V_{IN} must not exceed (B,G,L,O,X)V_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

2.1.1.1 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Proper device operation outside these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.0 V ± 30 mV 1.1 V ± 33 mV	V	1
PLL supply voltage	AV_{DD}_CORE, AV_{DD}_DDR, AV_{DD}_LBIU, AV_{DD}_PLAT, AV_{DD}_QE, AV_{DD}_SRDS	1.0 V ± 30 mV 1.1 V ± 33 mV	V	2

2.1.1.2 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 4. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Enhanced local bus interface utilities signals	45 45 45	BV_{DD} = 3.3 V BV_{DD} = 2.5 V BV_{DD} = 1.8 V	—
DDR2 signal	18 (full strength mode) 35 (half strength mode)	GV_{DD} = 1.8 V	1
DDR3 signal	20 (full strength mode) 40 (half strength mode)	GV_{DD} = 1.5 V	1
DUART, EPIC, I^2C, JTAG, system control	45	OV_{DD} = 3.3 V	—

Note:

1. The drive strength of the DDR2 or DDR3 interface in half-strength mode is at T_J = 105°C and at GV_{DD} (min). Refer to the MPC8569 reference manual for the DDR impedance programming procedure through the DDR control driver register 1 (DDRCDR_1).

2.1.2 Power Sequencing

The MPC8569E requires its power rails to be applied in a specific sequence to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DD}_n, BV_{DD}, $LV_{DD}n$, OV_{DD}, ScoreVDD, XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

While V_{DD} is ramping, current may be supplied from V_{DD} through the MPC8569E to GV_{DD}. Nevertheless, GV_{DD} from an external supply should follow the sequencing described above.

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power up, and extra current may be drawn by the device.

2.1.3 RESET Initialization

This section describes the AC electrical specifications for the RESET timing requirements of the MPC8569E. The following table describes the specifications for the RESET initialization timing.

Table 5. RESET Initialization Timing Specifications

Parameter	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	10	—	SYSCLK	1, 2
Minimum assertion time of $\overline{\text{TRESET}}$ simultaneous to HRESET assertion	25	—	ns	3

The following figure shows the DDR2 and DDR3 SDRAM interface output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

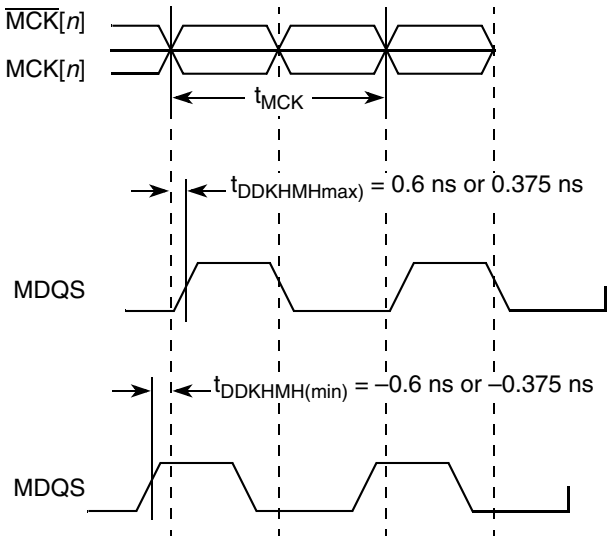


Figure 9. Timing Diagram for t_{DDKHMH}

The following figure shows the DDR2 and DDR3 SDRAM output timing diagram.

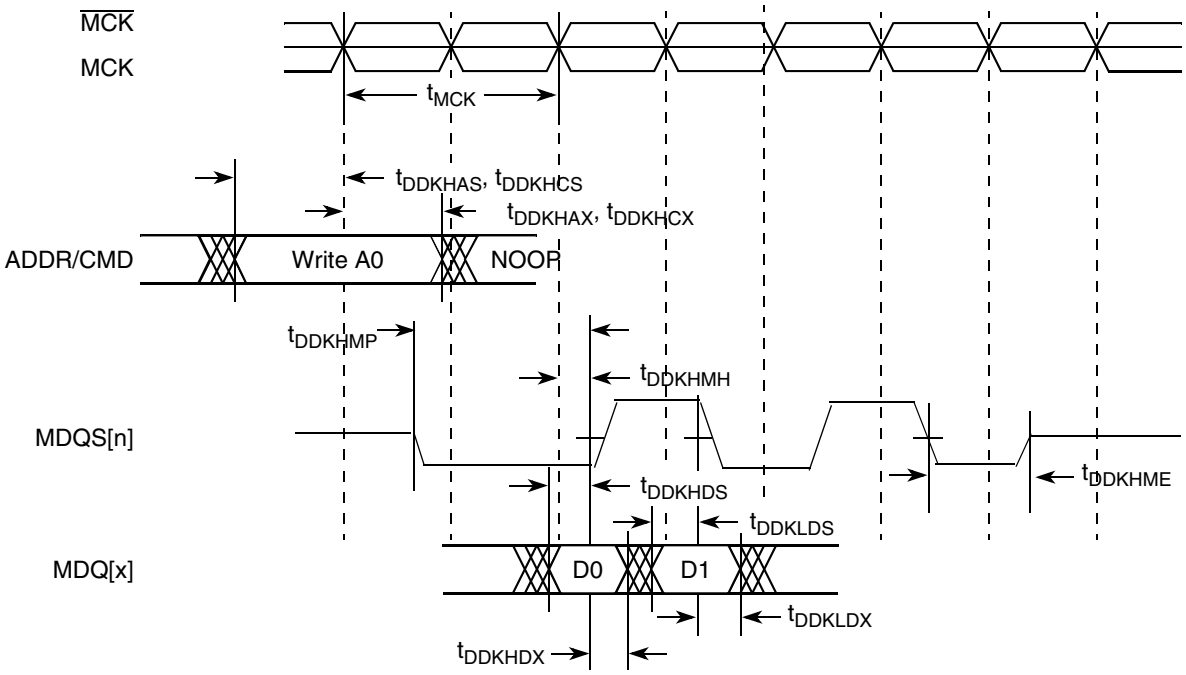


Figure 10. DDR2 and DDR3 Output Timing Diagram

The following figure shows the data and command input AC timing diagram.

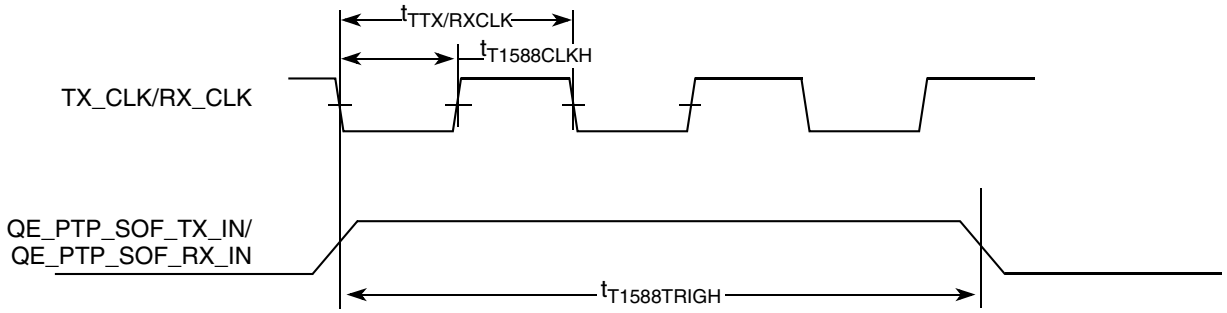


Figure 33. QUICC Engine Block IEEE 1588 Input AC Timing (SOF TRIG)

2.7 Ethernet Management Interface

The electrical characteristics specified in this section apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI, and RTBI are specified in Section 2.6, "Ethernet Interface."

2.7.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The following table provides the DC electrical characteristics for MDIO and MDC.

Table 42. MII Management DC Electrical Characteristics

At recommended operating conditions with LV_{DD} = 3.3 V

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage	V_{IH}	2.0	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current (LV_{DD} = Max, V_{IN} = 2.1 V)	I_{IH}	—	40	μA	1
Input low current (LV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA	1
Output high voltage (LV_{DD} = Min, I_{OH} = –4.0 mA)	V_{OH}	2.4	—	V	—
Output low voltage (LV_{DD} = Min, I_{OL} = 4.0 mA)	V_{OL}	—	0.4	V	—

Note:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 2 and Table 3.

Table 45. HDLC, BISYNC, and Transparent AC Timing Specifications (continued)

For recommended operating conditions, see Table 3

Characteristic	Symbol[1]	Min	Max	Unit	Notes
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns	—
Inputs—Internal clock input hold time	t_{HIIXKH}	0	—	ns	—
Inputs—External clock input hold time	t_{HEIXKH}	1.3	—	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
2. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.

The following table provides the input and output AC timing specifications for the synchronous UART protocols.

Table 46. Synchronous UART AC Timing Specifications

For recommended operating conditions, see Table 3

Characteristic	Symbol[1]	Min	Max	Unit	Notes
Outputs—Internal clock delay	t_{HIKHOV}	0	11	ns	2
Outputs—External clock delay	t_{HEKHOV}	1	14	ns	2
Outputs—Internal clock high Impedance	t_{HIKHOX}	0	11	ns	2
Outputs—External clock high Impedance	t_{HEKHOX}	1	14	ns	2
Inputs—Internal clock input setup time	t_{HIIVKH}	10	—	ns	—
Inputs—External clock input setup time	t_{HEIVKH}	8	—	ns	—
Inputs—Internal clock input hold time	t_{HIIXKH}	0	—	ns	—
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
2. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.

The following figure provides the AC test load.

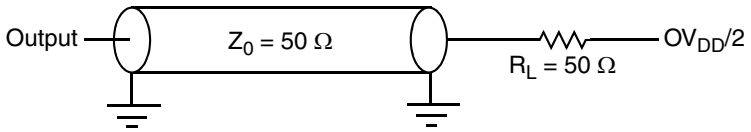


Figure 35. AC Test Load

may often differ from one component's output to the other's input. It may be different between the receiver input and driver output circuits within the same component. It is also referred to as the DC offset on some occasions.

To illustrate these definitions using real values, consider the example of a current mode logic (CML) transmitter that has a common mode voltage of 2.25 V and outputs, TD and $\overline{\text{TD}}$. If these outputs have a swing from 2.0 V to 2.5 V, the peak-to-peak voltage swing of each signal (TD or $\overline{\text{TD}}$) is 500 mV p-p, which is referred to as the single-ended swing for each signal. Because the differential signaling environment is fully symmetrical in this example, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 mV and –500 mV. In other words, V_{OD} is 500 mV in one phase and –500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage ($V_{DIFFp-p}$) is 1000 mV p-p.

2.9.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes.The SerDes reference clock inputs are SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ for PCI Express, Serial RapidIO, and SGMII interface, respectively.

The following sections describe the SerDes reference clock requirements and provide application information.

2.9.2.1 SerDes Spread Spectrum Clock Source Recommendations

SD_REF_CLK/$\overline{\text{SD\_REF\_CLK}}$ are designed to work with spread spectrum clock for PCI Express protocol only with the spreading specification defined in Table 47. When using spread spectrum clocking for PCI Express, both ends of the link partners should use the same reference clock. For best results, a source without significant unintended modulation must be used.

The spread spectrum clocking cannot be used if the same SerDes reference clock is shared with other non-spread spectrum supported protocols. For example, if the spread spectrum clocking is desired on a SerDes reference clock for PCI Express and the same reference clock is used for any other protocol such as SGMII/SRIO due to the SerDes lane usage mapping option, spread spectrum clocking cannot be used at all.

Table 47. SerDes Spread Spectrum Clock Source Recommendations

At recommended operating conditions. See Table 3.

Parameter	Min	Max	Unit	Notes
Frequency modulation	30	33	kHz	—
Frequency spread	+0	–0.5	%	1

Note:

1. Only down spreading is allowed.

2.9.2.2 SerDes Reference Clock Receiver Characteristics

The following figure shows a receiver reference diagram of the SerDes reference clocks.

— For external DC-coupled connection, as described in Section 2.9.2.2, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 and 400 mV. The following figure shows the SerDes reference clock input requirement for DC-coupled connection scheme.

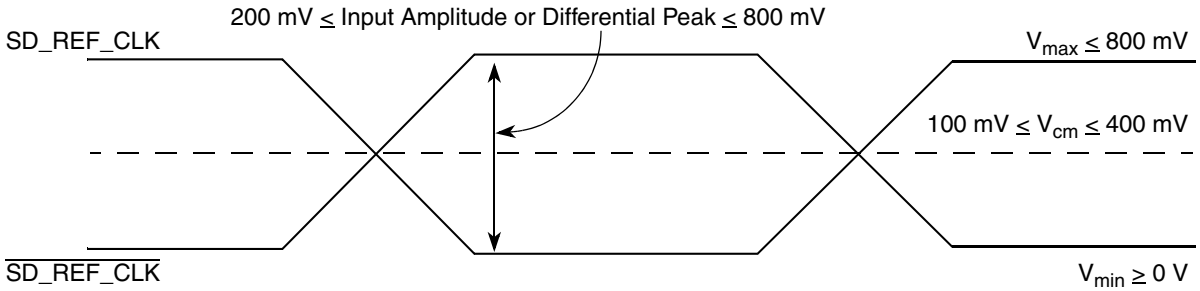


Figure 40. Differential Reference Clock Input DC Requirements (External DC-Coupled)

— For external AC-coupled connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SCOREGND. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SCOREGND). The following figure shows the SerDes reference clock input requirement for AC-coupled connection scheme.

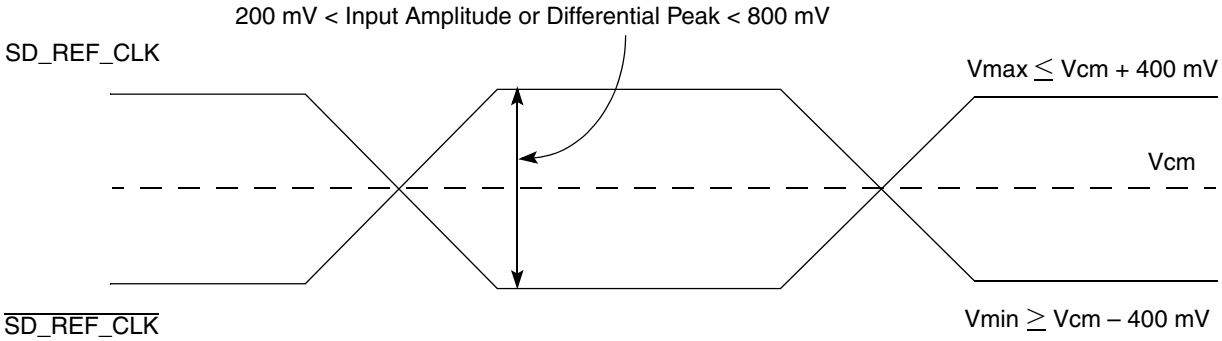


Figure 41. Differential Reference Clock Input DC Requirements (External AC-Coupled)

- Single-ended mode
  - — The reference clock can also be single-ended. The SD_REF_CLK input amplitude (single-ended swing) must be between 400 and 800 mV peak-peak (from V_{min} to V_{max}) with $\overline{\text{SD\_REF\_CLK}}$ either left unconnected or tied to ground.
  - — The SD_REF_CLK input average voltage must be between 200 and 400 mV. Figure 42 shows the SerDes reference clock input requirement for single-ended signaling mode.
  - — To meet the input amplitude requirement, the reference clock inputs might need to be DC- or AC-coupled externally. For the best noise performance, the reference of the clock could be DC- or AC-coupled into the unused phase ($\overline{\text{SD\_REF\_CLK}}$) through the same source impedance as the clock input (SD_REF_CLK) in use.

(RD and $\overline{RD}$). Each signal swings between A volts and B volts where A > B. Using these waveforms, the definitions are as follows:

1. The transmitter output signals and the receiver input signals TD, $\overline{TD}$, RD, and $\overline{RD}$ each have a peak-to-peak swing of A – B volts
2. The differential output signal of the transmitter, V_{OD}, is defined as $V_{TD} - V_{\overline{TD}}$
3. The differential input signal of the receiver, V_{ID}, is defined as $V_{RD} - V_{\overline{RD}}$
4. The differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) volts
5. The peak value of the differential transmitter output signal and the differential receiver input signal is A – B volts
6. The peak-to-peak value of the differential transmitter output signal and the differential receiver input signal is 2 × (A – B) volts

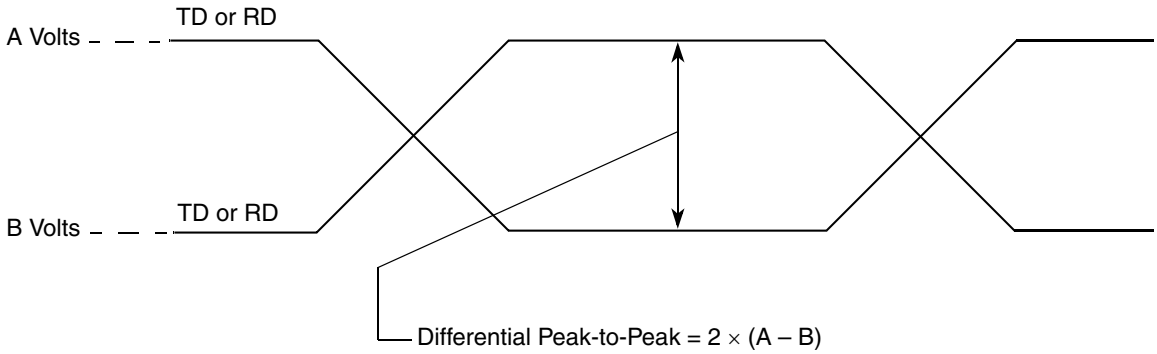


Figure 47. Differential Peak-Peak Voltage of Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (current mode logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and $\overline{TD}$, has a swing that goes between 2.5 and 2.0 V. Using these values, the peak-to-peak voltage swing of the signals TD and $\overline{TD}$ is 500 mV p-p. The differential output signal ranges between 500 and –500 mV. The peak differential voltage is 500 mV. The peak-to-peak differential voltage is 1000 mV p-p.

2.11.2 Equalization

With the use of high speed serial links, the interconnect media will cause degradation of the signal at the receiver. Effects such as inter-symbol interference (ISI) or data dependent jitter are produced. This loss can be large enough to degrade the eye opening at the receiver beyond what is allowed in the specification. To negate a portion of these effects, equalization can be used. The most common equalization techniques that can be used are:

- Pre-emphasis on the transmitter
- A passive high pass filter network placed at the receiver. This is often referred to as passive equalization.
- The use of active circuits in the receiver. This is often referred to as adaptive equalization.

2.11.4.2 AC Requirements for Serial RapidIO Transmitter

The following table defines the transmitter AC specifications for the Serial RapidIO. The AC timing specifications do not include RefClk jitter

Table 55. SRIO Transmitter AC Timing Specifications

At recommended operating conditions with XV_{DD} = 1.0 V ± 3%. and 1.1 V ± 3%

Parameter	Symbol	Min	Typical	Max	Unit	Notes
Deterministic jitter	J_D	—	—	0.17	UI p-p	—
Total jitter	J_T	—	—	0.35	UI p-p	—
Unit Interval: 1.25 GBaud	UI	800 – 100ppm	800	800 + 100ppm	ps	—
Unit Interval: 2.5 GBaud	UI	400 – 100ppm	400	400 + 100ppm	ps	—
Unit Interval: 3.125 GBaud	UI	320 – 100ppm	320	320 + 100ppm	ps	—

The following table defines the receiver AC specifications for Serial RapidIO. The AC timing specifications do not include RefClk jitter.

Table 56. SRIO Receiver AC Timing Specifications

At recommended operating conditions with ScoreVDD = 1.0 V ± 3%. and 1.1 V ± 3%.

Parameter	Symbol	Min	Typical	Max	Unit	Notes
Deterministic jitter tolerance	J_D	0.37	—	—	UI p-p	1, 3
Combined deterministic and random jitter tolerance	J_{DR}	0.55	—	—	UI p-p	1, 3
Total jitter tolerance[2]	J_T	0.65	—	—	UI p-p	1, 3
Bit error rate	BER	—	—	10^{-12}	—	—
Unit Interval: 1.25 GBaud	UI	800 – 100ppm	800	800 + 100ppm	ps	—
Unit Interval: 2.5 GBaud	UI	400 – 100ppm	400	400 + 100ppm	ps	—
Unit Interval: 3.125 GBaud	UI	320 – 100ppm	320	320 + 100ppm	ps	—

Notes:
1. Measured at receiver
2. Total jitter is composed of three components: deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 48. The sinusoidal jitter component is included to ensure margin for low-frequency jitter, wander, noise, crosstalk, and other variable system effects.
3. System/board must be designed to ensure the input requirement to the device is achieved. Proper device operation is guaranteed for inputs meeting this requirement by design, simulation, characterization, or functional testing

Table 62. JTAG AC Timing Specifications (continued)

For recommended operating conditions, see Table 3

Parameter	Symbol[1]	Min	Max	Unit	Notes
Input hold times	t_{JTDXKH}	10	—	ns	—
Output valid times: Boundary-scan data TDO	t_{JTKLDV}	 — —	 15 10	ns	3
Output hold times	t_{JTKLDX}	0	—	ns	3

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) reaching the invalid state (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
3. All outputs are measured from the midpoint voltage of the falling edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load. Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
4. System/board must be designed to ensure the input requirement to the device is achieved. Proper device operation is guaranteed for inputs meeting this requirement by design, simulation, characterization, or functional testing

The following figure provides the AC test load for TDO and the boundary-scan outputs of the device.

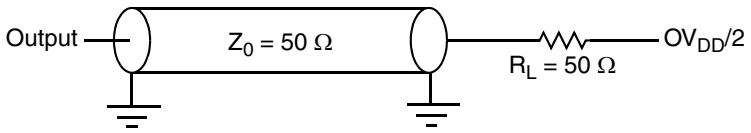


Figure 52. AC Test Load for the JTAG Interface

The following figure provides the JTAG clock input timing diagram.

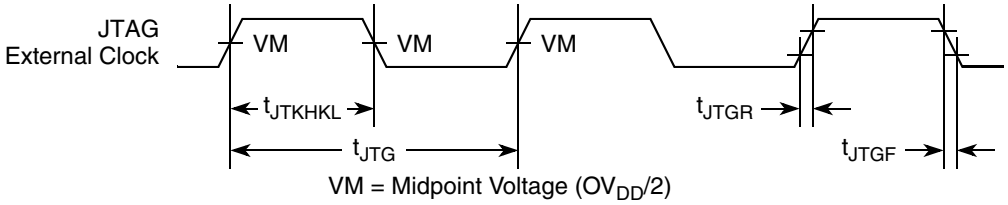


Figure 53. JTAG Clock Input Timing Diagram

The following figure provides the $\overline{\text{TRST}}$ timing diagram.

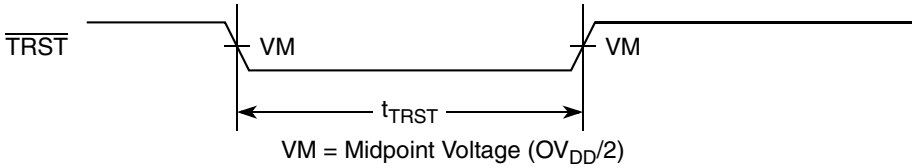


Figure 54. $\overline{\text{TRST}}$ Timing Diagram

2.15.2.2 Enhanced Local Bus AC Timing Specifications for PLL Enable Mode

For PLL enable mode, all timings are relative to the rising edge of LSYNC_IN.

The following table describes the timing specifications of the enhanced local bus interface at BV_{DD} = 3.3 V, 2.5 V and 1.8 V for PLL enable mode.

Table 66. Enhanced Local Bus Timing Specifications (BV_{DD} = 3.3 V 2.5 V and 1.8 V) —PLL Enabled Mode

For recommended operating conditions, see Table 3

Parameter	Symbol[1]	Min	Max	Unit	Notes
Enhanced local bus cycle time	t_{LBK}	7.5	12	ns	—
Enhanced local bus duty cycle	t_{LBKH}/t_{LBK}	45	55	%	5
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	680	ps	2
Input setup	t_{LBIVKH}	2	—	ns	—
Input hold	t_{LBIXKH}	1.0	—	ns	—
Output delay (Except LALE)	t_{LBKHOV}	—	3.8	ns	—
Output hold (Except LALE)	t_{LBKHOX}	0.6	—	ns	—
Enhanced local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	3
LALE output negation to LAD/LDP output transition (LATCH hold time)	t_{LBONOT}	1 – 0.475 ns (LBCR[AHD]=0) ½ – 0.475 ns (LBCR[AHD] = 1)	—	eLBC controller clock cycle (= 1 platform clock cycle in ns)	4

Notes:

1. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN to $BV_{DD}/2$ of the signal in question.
2. Skew measured between different LCLK signals at $BV_{DD}/2$.
3. For purposes of active/float timing measurements, the high impedance or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. t_{LBONOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBONOT} is determined by LBCR[AHD]. The unit is the eLBC controller clock cycle. The eLBC controller clock refers to the internal clock that runs the local bus controller, not the external LCLK. LCLK cycle = eLBC controller clock cycle × LCRR[CLKDIV]. After power on reset, LBCR[AHD] defaults to 0 and eLBC runs at maximum hold time.
5. System/board must be designed to ensure the input requirement to the device is achieved. Proper device operation is guaranteed for inputs meeting this requirement by design, simulation, characterization, or functional testing.

The following table describes the timing specifications of the enhanced local bus interface at BV_{DD} = 3.3, 2.5, and 1.8 V DC with PLL disabled.

Table 67. Enhanced Local Bus Timing Specifications (BV_{DD} = 3.3 V, 2.5 V, and 1.8 V)—PLL Bypassed

For recommended operating conditions, see Table 3

Parameter	Symbol[1]	Min	Max	Unit	Notes
Enhanced local bus cycle time	t_{LBK}	12	—	ns	—
Enhanced local bus duty cycle	t_{LBKH}/t_{LBK}	45	55	%	6
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	2
Input setup (except LUPWAIT/LFRB)	t_{LBIVKH}	6.5	—	ns	—
Input hold (except LUPWAIT/LFRB)	t_{LBIXKH}	1	—	ns	—
Input setup (for LUPWAIT/LFRB)	t_{LBIVKL}	6.5	—	ns	—
Input hold (for LUPWAIT/LFRB)	t_{LBIXKL}	1	—	ns	—
Output delay (Except LALE)	t_{LBKLOV}	—	1.5	ns	—
Output hold (Except LALE)	t_{LBKLOX}	–3.5	—	ns	5
Enhanced local bus clock to output high impedance for LAD/LDP	t_{LBKLOZ}	—	2	ns	3
LALE output negation to LAD/LDP output transition (LATCH hold time)	t_{LBONOT}	1 – 1 ns (LBCR[AHD] = 0) 1/2 – 1 ns (LBCR[AHD] = 1)	—	eLBC controller clock cycle (=1 platform clock cycle in ns)	4

Notes:

1. All signals are measured from $BV_{DD}/2$ of rising/falling edge of LCLK to $BV_{DD}/2$ of the signal in question.
2. Skew measured between different LCLK signals at $BV_{DD}/2$.
3. For purposes of active/float timing measurements, the high impedance or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. t_{LBONOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBONOT} is determined by LBCR[AHD]. The unit is the eLBC controller clock cycle, which is the internal clock that runs the local bus controller, not the external LCLK. LCLK cycle = eLBC controller clock cycle × LCRR[CLKDIV]. After power on reset, LBCR[AHD] defaults to 0 and eLBC runs at maximum hold time.
5. Output hold is negative. This means that output transition happens earlier than the falling edge of LCLK.
6. System/board must be designed to ensure the input requirement to the device is achieved. Proper device operation is guaranteed for inputs meeting this requirement by design, simulation, characterization, or functional testing.

The following figure shows the AC timing diagram for PLL bypass mode.

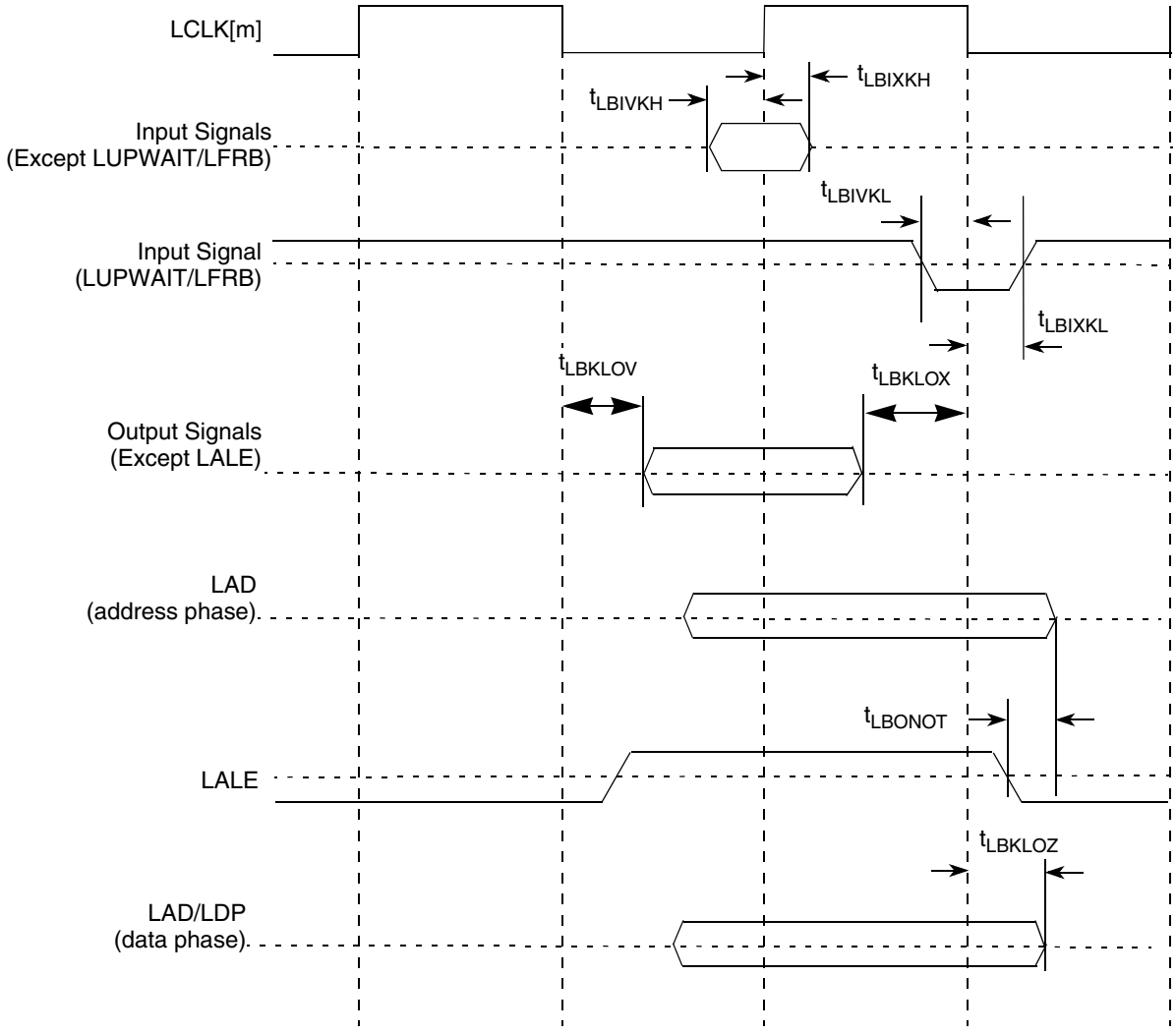


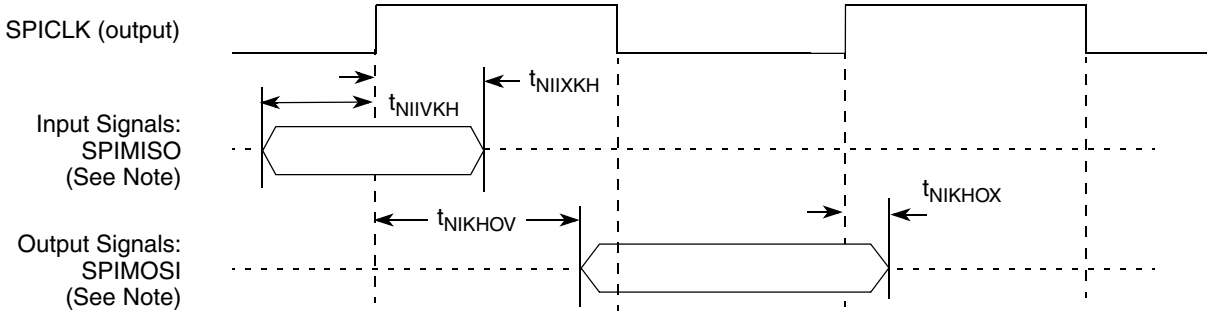
Figure 59. Enhanced Local Bus Signals (PLL Bypass Mode)

The above figure applies to all three controllers that eLBC supports: GPCM, UPM, and FCM.

For input signals, the AC timing data is used directly for all three controllers.

For output signals, each type of controller provides its own unique method to control the signal timing. The final signal delay value for output signals is the programmed delay plus the AC timing delay. For example, for GPCM, LCS can be programmed to delay by t_{acs} (0, ¼, ½, 1, 1 + ¼, 1 + ½, 2, 3 cycles), so the final delay is $t_{acs} + t_{LBKHOV}$.

The following figure shows the SPI timing in master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 66. SPI AC Timing in Master Mode (Internal Clock) Diagram

2.20 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8569E.

2.20.1 TDM/SI DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8569E TDM/SI.

Table 76. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Min	Max	Unit	Notes
Output high voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—
Output low voltage (OV_{DD} = min, I_{OH} = 2 mA)	V_{OL}	—	0.4	V	—
Input high voltage	V_{IH}	2.0	OV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.8	V	—
Input current (0 V ≤ V_{IN} ≤ OV_{DD})	I_{IN}	—	±40	μA	1

Note:
1. The symbol V_{IN}, in this case, represents the OV_{IN} referenced in Table 2 and Table 3.

2.20.2 TDM/SI AC Timing Specifications

The following table provides the TDM/SI input and output AC timing specifications.

NOTE: Rise/Fall Time on QE Input Pins

The rise / fall time on QE input pins should not exceed 5ns. This must be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of Vcc; fall time refers to transitions from 90% to 10% of Vcc.

The following figure depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.

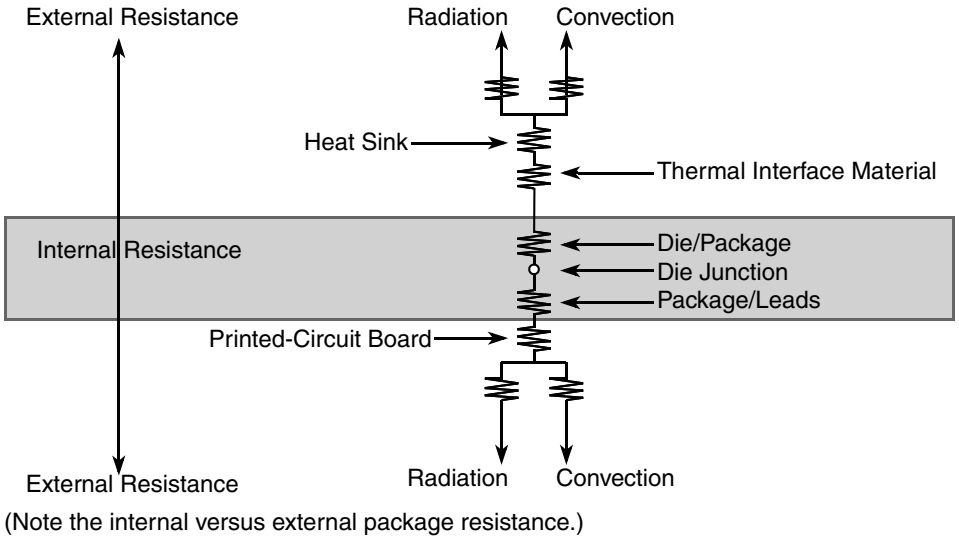


Figure 74. Package with Heat Sink Mounted to a Printed-Circuit Board

The heat sink removes most of the heat from the device. Heat generated on the active side of the chip is conducted through the silicon and the heat sink attach material (or thermal interface material), and to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

3.3.2 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. The performance of thermal interface materials improves with increased contact pressure; this performance characteristic chart is generally provided by the thermal interface vendor. The recommended method of mounting heat sinks on the package is by means of a spring clip attachment to the printed-circuit board (see Figure 73).

The system board designer can choose among several types of commercially-available thermal interface materials.

3.3.3 Temperature Diode

The device has a temperature diode on the microprocessor that can be used in conjunction with other system temperature monitoring devices (such as On Semiconductor, NCT1008™). These devices use the negative temperature coefficient of a diode operated at a constant current to determine the temperature of the microprocessor and its environment.

The following are the specifications of the MPC8569E on-board temperature diode:

Operating range: 10 – 230 μA

Ideality factor over 13.5 – 220 μA; n = 1.006 +/- 0.008

4 Package Description

The following section describes the detailed content and mechanical description of the package.